

LIST OF PATENTS AND PUBLICATIONS  
APPLICANT'S INFORMATION  
DISCLOSURE STATEMENT

Applicant: Jae-Hyun Ryou et al.

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T N	5,625,729	04/29/1997	Brown			
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TN	<input checked="" type="checkbox"/>	U.S. Patent Application Serial No. 09/751,422, filed December 29, 2000, entitled "Resonant Reflector for Use with Optoelectronic Devices".
	<input checked="" type="checkbox"/>	U.S. Patent Application Serial No. 09/751,423, filed December 29, 2000, entitled "Spatially Modulated Reflector for an Optoelectronic Device".

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